

PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of:

Taro OSABE et al.

Appln. No.:

Filed: HERewith

For: NON-VOLATILE SEMICONDUCTOR MEMORY

* * *

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

Pursuant to 37 C.F.R. § 1.56, and without any
assertion as to materiality or prior art effect, the
documents listed on the attached Form PTO-1449 are hereby
cited.

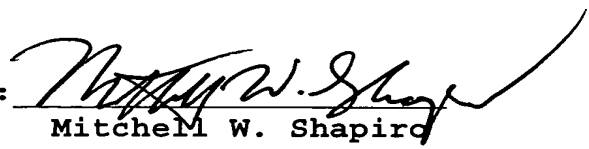
The documents on the attached List were cited in the
specification, on pages 2-5, and their relevance is
indicated therein.

Respectfully submitted,

MWS:sjk

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By:


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October 21, 2003

FORM PTO-1449				Atty. Docket No. XA-9953		Appln. No.	
<u>LIST OF DOCUMENTS CITED BY APPLICANT</u>							
				Applicant Taro OSABE et al.			
				Filing Date HEREWITH		Group	
U.S. PATENT DOCUMENTS							
Examiner Initial		Document Number	Date	Name	Class	Sub-class	Filing Date
	AA	6,344,993	02/05/02	Harari et al.	365	185.01	
	AB	5,949,711	09/07/99	Kazerounian	365	185.05	
	AC						
	AD						
	AE						
	AF						
FOREIGN PATENT DOCUMENTS							
Examiner Initial		Document Number	Date	Country	Class	Sub-class	Translation
	AG	2001-230332	08/24/01	Japan			Abstract
	AH	2001-237330	08/31/01	Japan			Abstract
	AI						
	AJ						
OTHER (including author, title, date, pertinent pages, etc.)							
	AK	J. Choi et al., "A 0.15 μm NAND Flash Technology with 0.11 μm^2 Cell Size for 1 Gbit Flash Memory", IEEE Technical Digest of International Device Meeting, 2000, pp. 767-770.					
	AL	T. Jung et al., "A 3.3V 128Mb Multi-Level NAND Flash Memory for Mass Storage Applications", IEEE International Solid-State-Circuit Conference, 1996, pp. 32-33.					
	AM	B. Eitan et al., "Can NROM, a 2 Bit, Trapping Storage NVM Cell, Give a Real Challenge to Floating Gate Cells?", International Conference on Solid State Devices and Materials, Tokyo 1999, pp. 522-523 (extended abstract).					
	AN	T. Kobayashi et al., "A Giga-Scale Assist-Gate (AG)-AND-Type Flash Memory Cell with 20-MB/s Programming Throughput for Content-Downloading Applications", IEEE Technical Digest of International Electron Device Meeting, 2001, pp. 29-32.					
Examiner				Date Considered			
EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.							